IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Group Art Unit: Unassigned : Ming-Chi LIAW et al.

Continuation Application of: Application S.N. 09/155,181

Examiner: Unassigned

Filed: March 26, 1999

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Continuation Application Filed:

17 July 2003

SOLUTIONS AND PROCESSES FOR REMOVAL OF SIDEWALL For: RESIDUE AFTER DRY ETCHING

PRELIMINARY AMENDMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SIR:

Please amend the above identified application as indicated below prior to examination.

IN THE CLAIMS

Please cancel claims 1-12 without prejudice or disclaimer.

Please add the following new claims:

A process for removing photoresist after drywall etching comprising treating a **13.** wafer after dry etching with a solution comprising sulfuric acid and a mixture of a fluorine containing compound and hydrogen peroxide.